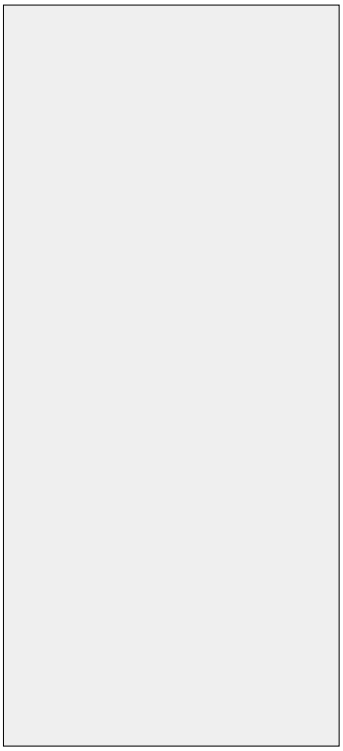
JCT151F-650RH 12A SCR

Rev.A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT151F-650RH of silicon controlled rectifiers provides high dV/dt rate wi



Average gate power dissipation (T_j=150) $P_{G(AV)}$

ORDERING INFORMATION

J CT 151 F -650R H

JieJie Microelectronics Co., Ltd.

SCRs

650R:V

FIG.1: Maximum power dissipation versus RMS on-state current

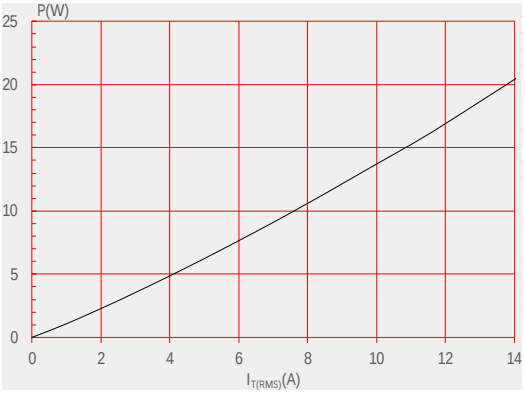


FIG.2: RMS on-state current versus case temperature

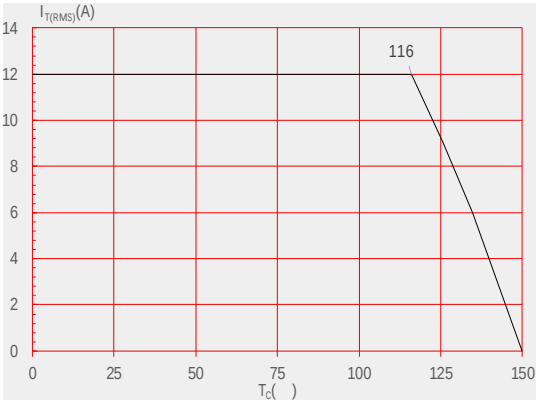


FIG.3: Surge peak on-state current versus number of cycles

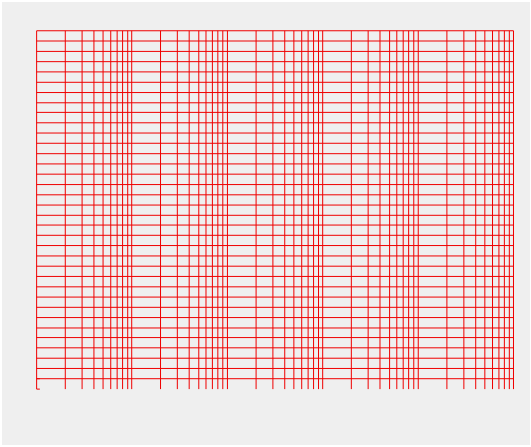
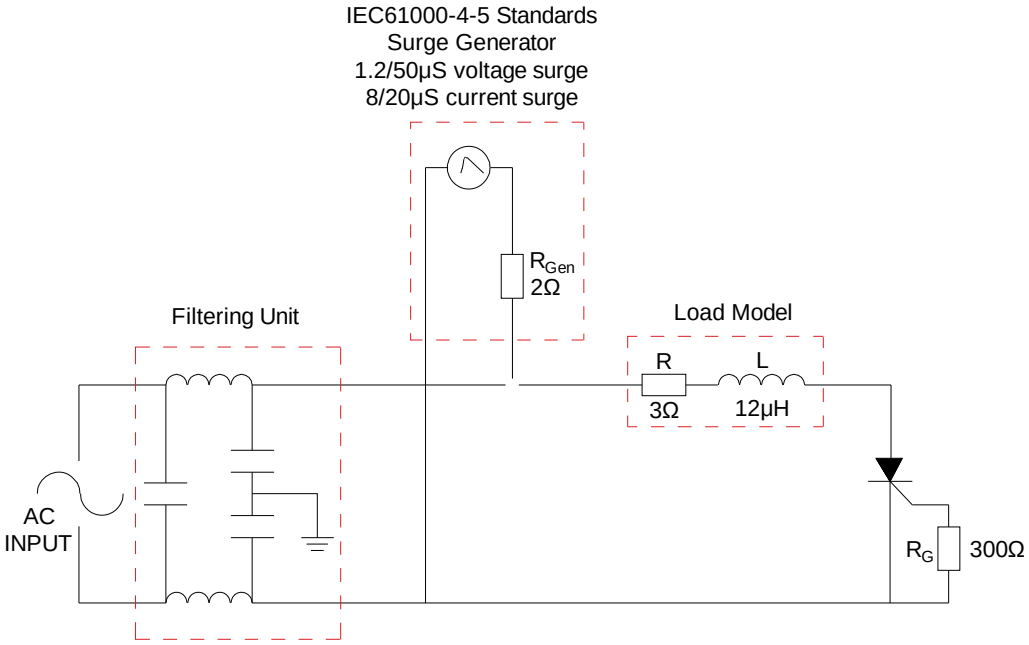


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT151F-650RH	650	15	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Aug.22, 2025	A.1.0	Last update
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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